

EVVOSEMI[®]

THINK CHANGE DO



ESD



TVS



MOS



LDO



Diode



Sensor



DC-DC

Product Specification

▶ Domestic	Part Number	2N65
▶ Overseas	Part Number	2N65
▶ Equivalent	Part Number	2N65

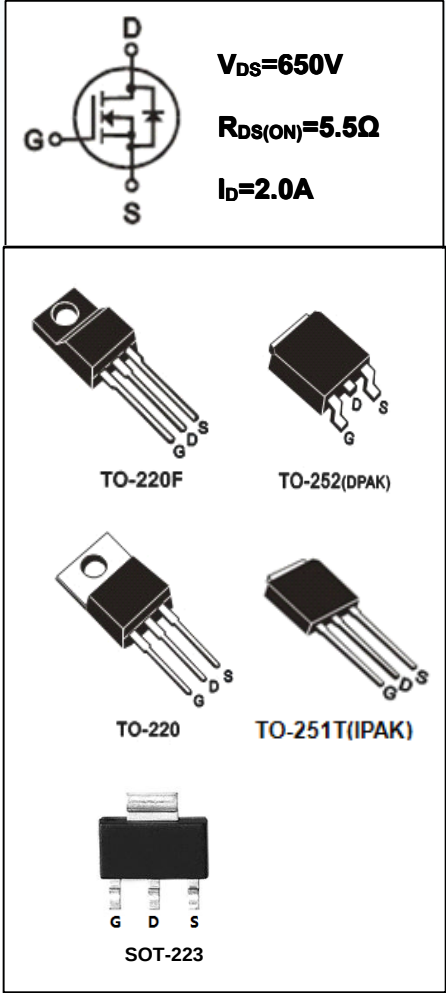
EV is the abbreviation of name EVVO

N-沟道功率 MOS 管

- 最大额定值 (TC=25°C)
- Absolute Maximum Ratings (Tc=25°C) TO-220/220F/251T/252/223

参数 PARAMETER	符号 SYMBOL	额定值 VALUE	单位 UNIT
源电压 Drain-source Voltage	V _{DS}	650	V
源栅电压 gate-source Voltage	V _{GS}	30±	V
漏极电流 Continuous Drain Current TC=25°C	I _D	2.0*	A
漏极电流 Continuous Drain Current TC=100°C	I _D	1.25*	A
最大脉冲电流 Drain Current Pulsed ①	I _{DM}	8.0*	A
耗散功率 Power Dissipation	P _{tot}	TO-220/220F	W
		TO-251T/252	
		SOT-223	
最高结温 Junction Temperature	T _j	150	°C
存储温度 Storage Temperature	T _{STG}	-55-150	°C
单脉冲雪崩能量 Single Pulse Avalanche Energy ②	E _{AS}	120	mJ

*Drain current limited by maximum junction temperature



- 电特性 (Tc=25°C)
- Electronic Characteristics (Tc=25°C)

参数 PARAMETER	符号 SYMBOL	测试条件 TEST CONDITION	最小值 MIN	典型值 TYP	最大值 MAX	单位 UNIT
源漏击穿电压 Drain-source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250μA	650			V
击穿电压温度系数 Breakdown Voltage Temperature Coefficient	BVΔ _{DSS/ΔTj}	I _D =250uA, Referenced to 25°C		0.6		V/°C
栅极开启电压 Gate Threshold Voltage	V _{GS(TH)}	V _{GS} =V _{DS} , I _D =250μA	2.0		4.0	V
- 漏源漏电流 Drain-source Leakage Current	I _{DSS}	V _{DS} =650V, V _{GS} =0V, T _j =25°C			25	μA
		V _{DS} =520V, V _{GS} =0V, T _j =125°C			250	μA
跨导 Forward Transconductance	g _{fs}	V _{DS} =40V, I _D =1A ③		1.5		S

N-沟道功率 MOS 管

参数 PARAMETER	符号 SYMBOL	测试条件 TEST CONDITION	最小值 MIN	典型值 TYP	最大值 MAX	单位 UNIT
栅极漏电流 Gate-body Leakage Current ($V_{DS} = 0$)	I_{GSS}	$V_{GS} = \pm 30V$			± 100	nA
源漏通电阻 Static Drain-source On Resistance	$R_{DS(ON)}$	$V_{GS} = 10V, I_D = 1.0A$ ③		4.5	5.5	Ω
输入电容 Input Capacitance	C_{iss}	$V_{GS} = 0V, V_{DS} = 25V$ $F = 1.0MHz$		311		pF
关断延迟 Turn -Off Delay Time	$T_d(off)$	$V_{DD} = 300V, I_D = 2.0A$ $R_G = 25\Omega$ ③		24		ns
栅极电荷 Total Gate Charge	Q_g	$I_D = 2.0A, V_{DS} = 520V$ $V_{GS} = 10V$ ③		14.5		nC
栅源电荷 Gate-to-Source Charge	Q_{gs}			1.8		nC
栅漏电荷 Gate-to-Drain Charge	Q_{gd}			8.3		nC
二极管正向电流 Continuous Diode Forward Current	I_S				2.0	A
二极管正向压降 Diode Forward Voltage	V_{SD}	$T_j = 25^\circ C, I_S = 2.0A$ $V_{GS} = 0V$ ③			1.4	V
反向恢复时间 Reverse Recovery Time	t_{rr}	$T_j = 25^\circ C, I_f = 2.0A$ $di/dt = 100A/\mu s$ ③		368		ns
反向恢复电荷 Reverse Recovery Charge	Q_{rr}			1.0		μC

●热特性

●Thermal Characteristics

参数 PARAMETER	符号 SYMBOL	最大值 MAX		单位 UNIT
		TO-220	TO-220F	
壳 热阻结 Thermal Resistance Junction-case	R_{thJC}	2.31	4.46	$^\circ C/W$
- 热阻结 环境 Thermal Resistance Junction-ambient	R_{thJA}	62.5	62.5	$^\circ C/W$

(注释(Notes):

① 脉冲宽度：以最高结温为限制

Repetitive rating: Pulse width limited by maximum junction temperature

② Starting $T_j = 25^\circ C$, $V_{DD} = 50V$, $L = 56mH$, $R_G = 25\Omega$, $I_{AS} = 2.0A$ ③ 脉冲测试：脉冲宽度 $\leq 300\mu s$ ，占空比 $\leq 2\%$ Pulse Test : Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$

N-沟道功率 MOS 管

● 特性曲线

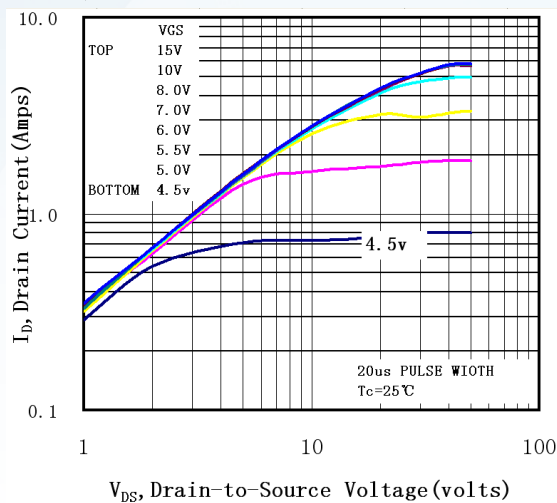


Fig1 Typical Output Characteristics, $T_c=25^\circ\text{C}$

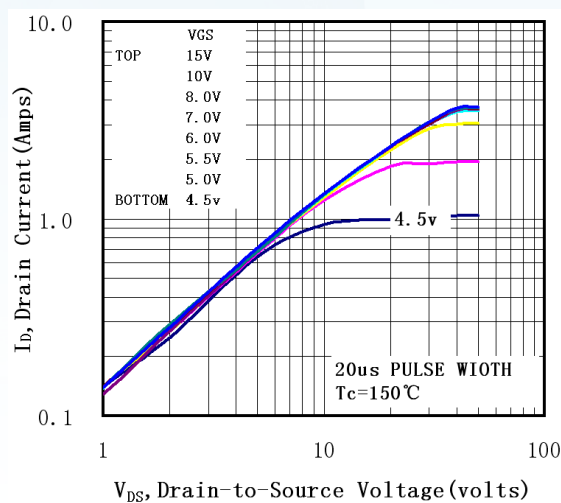


Fig2 Typical Output Characteristics, $T_c=150^\circ\text{C}$

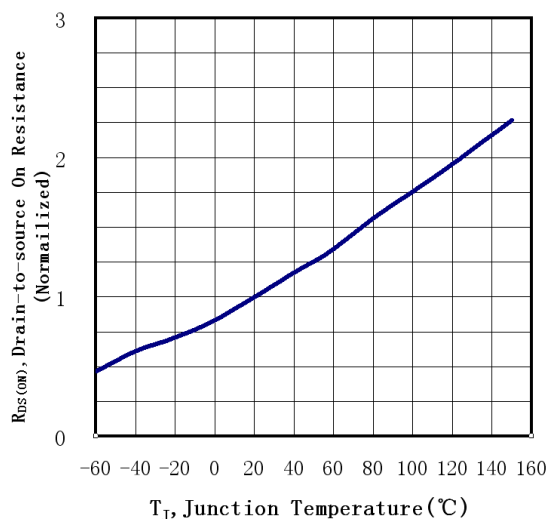


图3 导通电阻与温度曲线

Fig3 Normalized On-Resistance Vs. Temperature

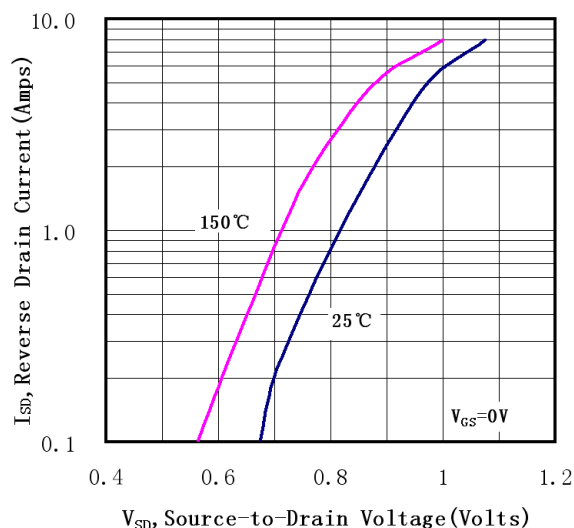


图4 二极管正向电压曲线

Fig4 Typical Source-Drain Diode Forward Voltage

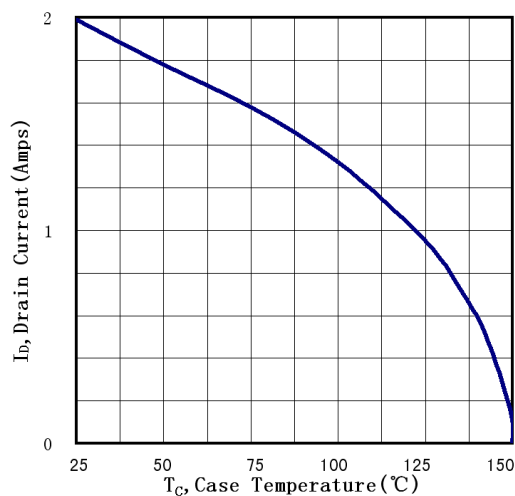


图5 最大漏极电流与壳温曲线

Fig5 Maximum Drain Current Vs. Case Temperature

N-沟道功率 MOS 管

● 特性曲线

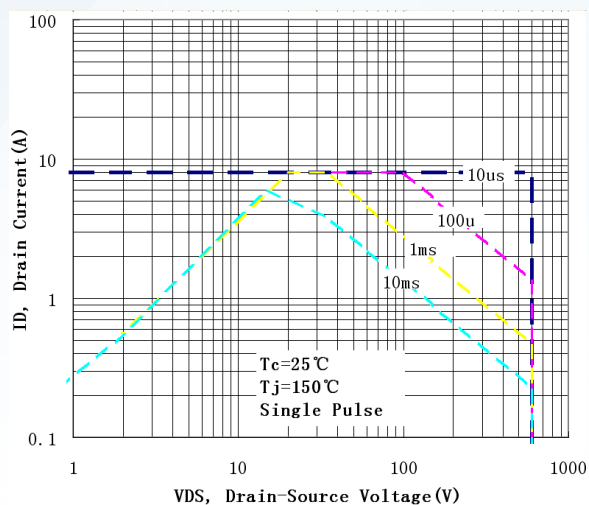


图 6-1 2N65(TO-126&126S)

最大安全工作区曲线

Fig6-1 Maximum Safe Operating Area

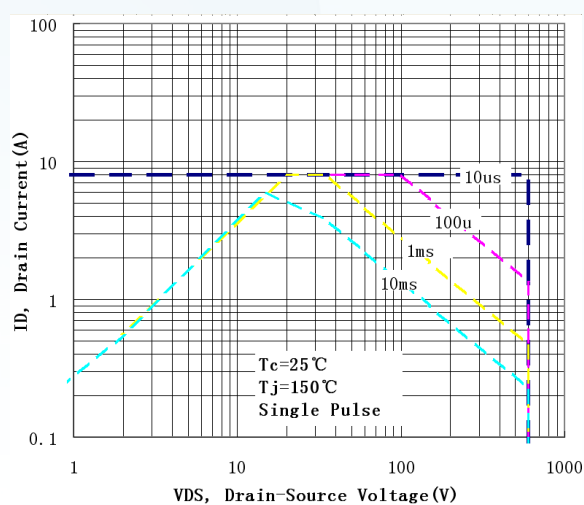


图 6-2 2N65(TO-220)

最大安全工作区曲线

Fig6-2 Maximum Safe Operating Area

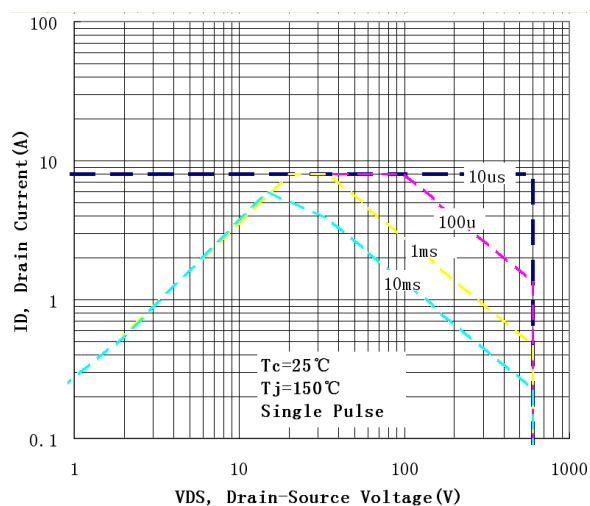


图 6-3 2N65(TO-220F)

最大安全工作区曲线

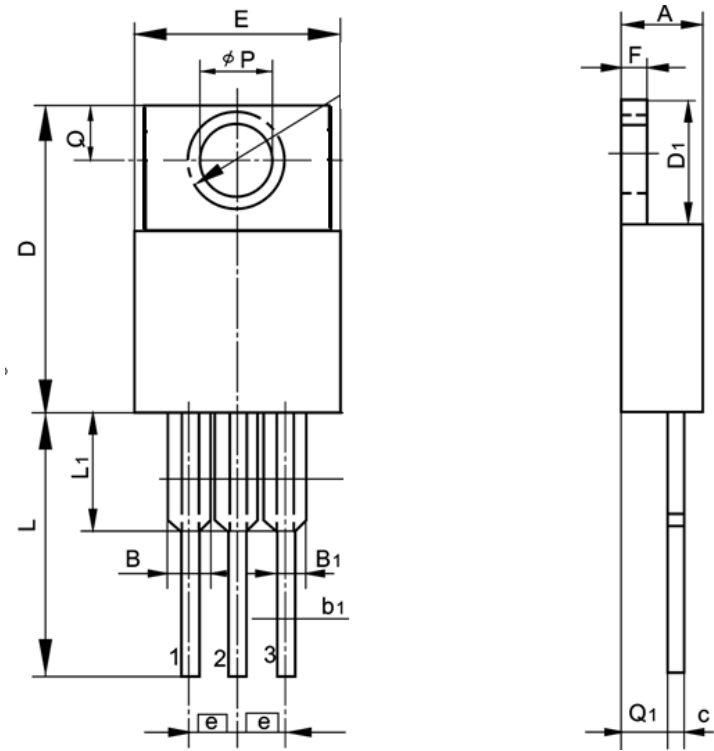
Fig6-3 Maximum Safe Operating Area

N-沟道功率 MOS 管

TO-220 封装

/UNIT 单位：毫米 mm

符号 SYMBOL	最小值 min	典型值 nom	最大值 max	符号 SYMBOL	最小值 min	典型值 nom	最大值 max
A	4.00		4.80	E	9.90		10.70
B	1.20		1.50	e		2.54	
B1	1.00		1.40	F	1.10		1.45
b1	0.65		1.00	L	12.50		14.50
c	0.35		0.75	L1	3.00	3.50	4.00
D	15.00		16.50	Q	2.50		3.00
D1	5.90		6.90	Q1	2.00		3.00
				P φ	3.60		3.90

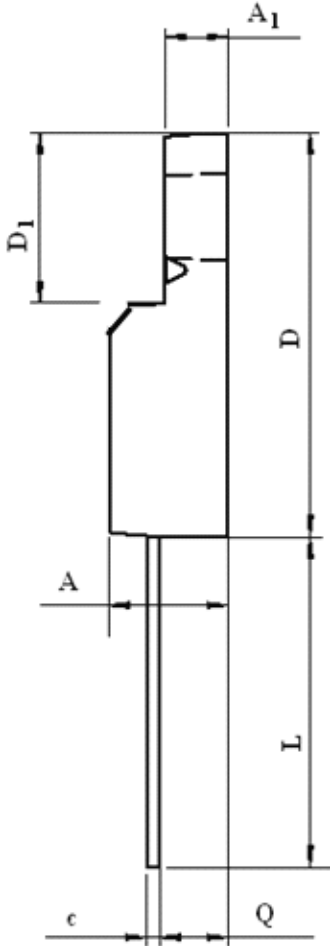
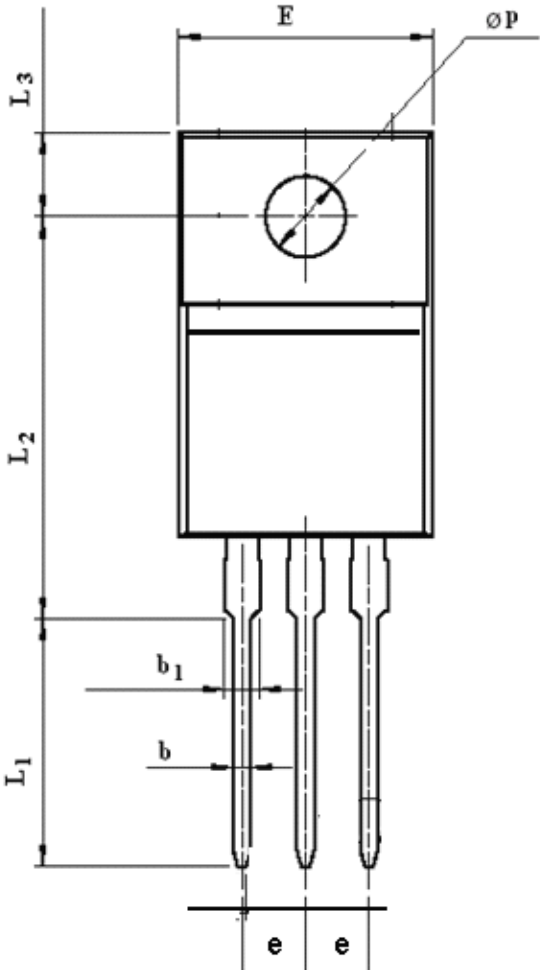


N-沟道功率 MOS 管

TO-220F 封装

单位:毫米/UNIT: mm

符号 SYMBOL	最小值 min	典型值 nom	最大值 max	符号 SYMBOL	最小值 min	典型值 nom	最大值 max
A	4.40		4.95	e		2.54	
A ₁	2.30		2.90	L	12.50		14.30
b	0.45		0.90	L ₁	9.10		10.05
b ₁	1.10		1.70	L ₂	15.00		16.00
c	0.35		0.90	L ₃	3.00		4.00
D	14.50		17.00	øp	3.00		3.50
D1	6.10		9.00	Q	2.30		2.80
E	9.60		10.30				



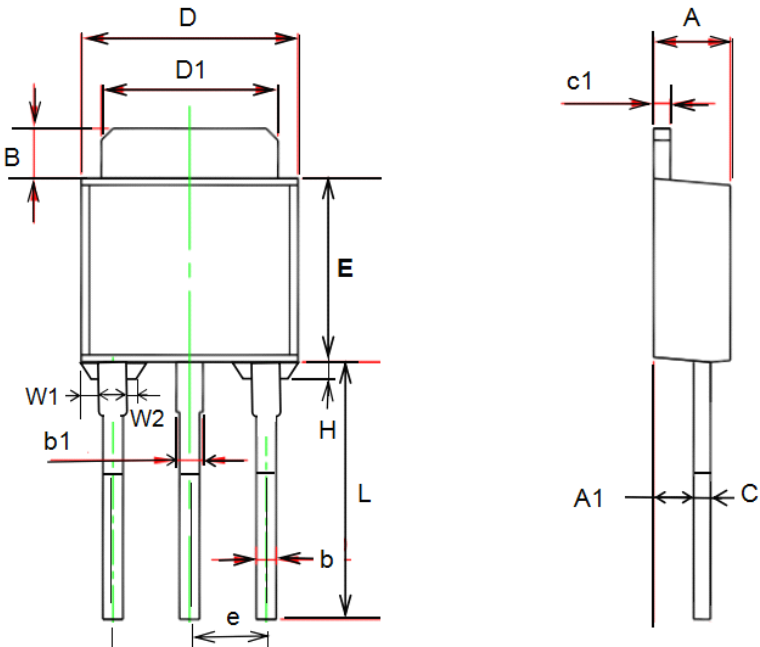
N-沟道功率 MOS 管

TO-251T 封装机械尺寸
TO-251T (IPAK) MECHANICAL DATA

单位:毫米/UNIT: mm

符号/SYMBOL	/	最小值/min	典型值/nom	最大值/max
A		2.10		2.50
A ₁		0.95		1.30
B		0.80		1.25
b		0.50		0.80
b ₁		0.70		0.80
c		0.45		0.70
c1		0.45		0.70
D		6.35		6.80
D ₁		5.10		5.50
E		5.30		6.30
e		2.25	2.30	2.35
L		7.00		9.20
H		0.35		0.45
W1		0.30		0.50
W2		0.20		0.40

[S/L]

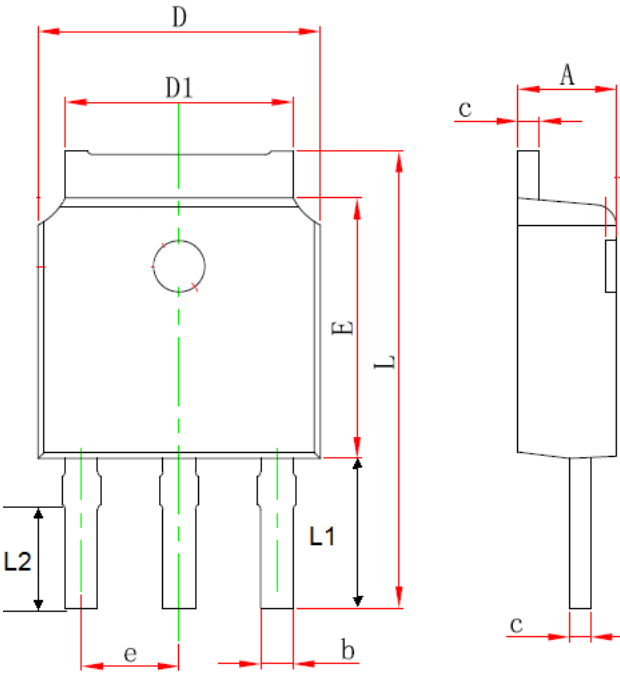


N-沟道功率 MOS 管

TO-251S 封装机械尺寸
TO-251S (IPAK) MECHANICAL DATA

单位:毫米/UNIT: mm

符号/SYMBOL	/	最小值/min	典型值/nom	最大值/max
A		2.20		2.40
b		0.60		0.85
C		0.45	0.50	0.60
D		6.50		6.70
D1		5.10		5.50
E		5.9		6.20
e		2.18	2.29	2.38
L		11.00		12.40
L1		4.8		5.3
L2		3.5		4.2

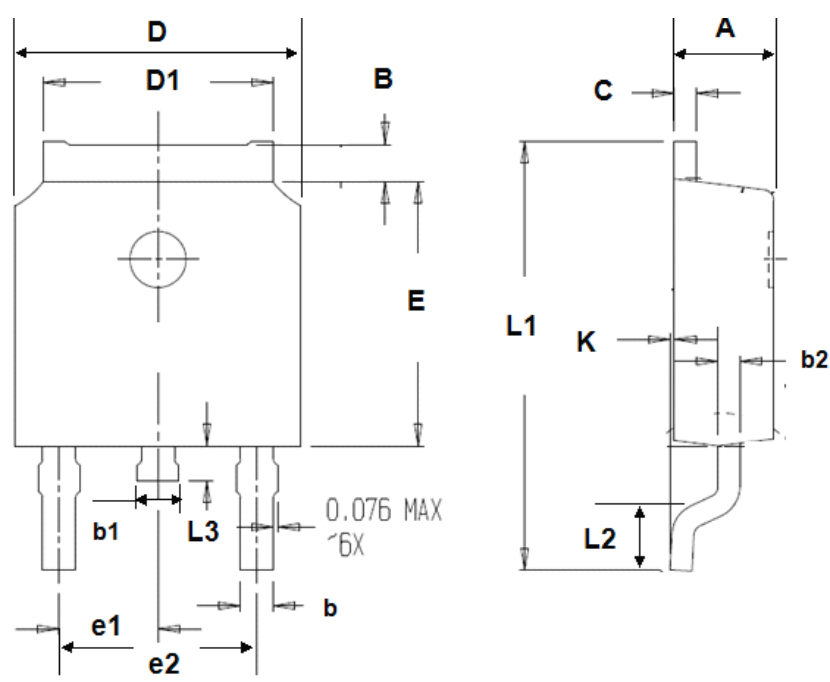


N-沟道功率 MOS 管

TO-252 封装机械尺寸
TO-252 MECHANICAL DATA

单位:毫米/UNIT: mm

符号 SYMBOL	最小值 min	最大值 max	符号 SYMBOL	最小值 min	最大值 max
A	2.10	2.50	B	0.85	1.25
b	0.50	0.80	b1	0.50	0.90
b2	0.45	0.70	C	0.45	0.70
D	6.30	6.75	D1	5.10	5.50
E	5.30	6.30	e1	2.25	2.35
L1	9.20	10.60	e2	4.45	4.75
L2	0.90	1.75	L3	0.60	1.10
K	0.00	0.23			

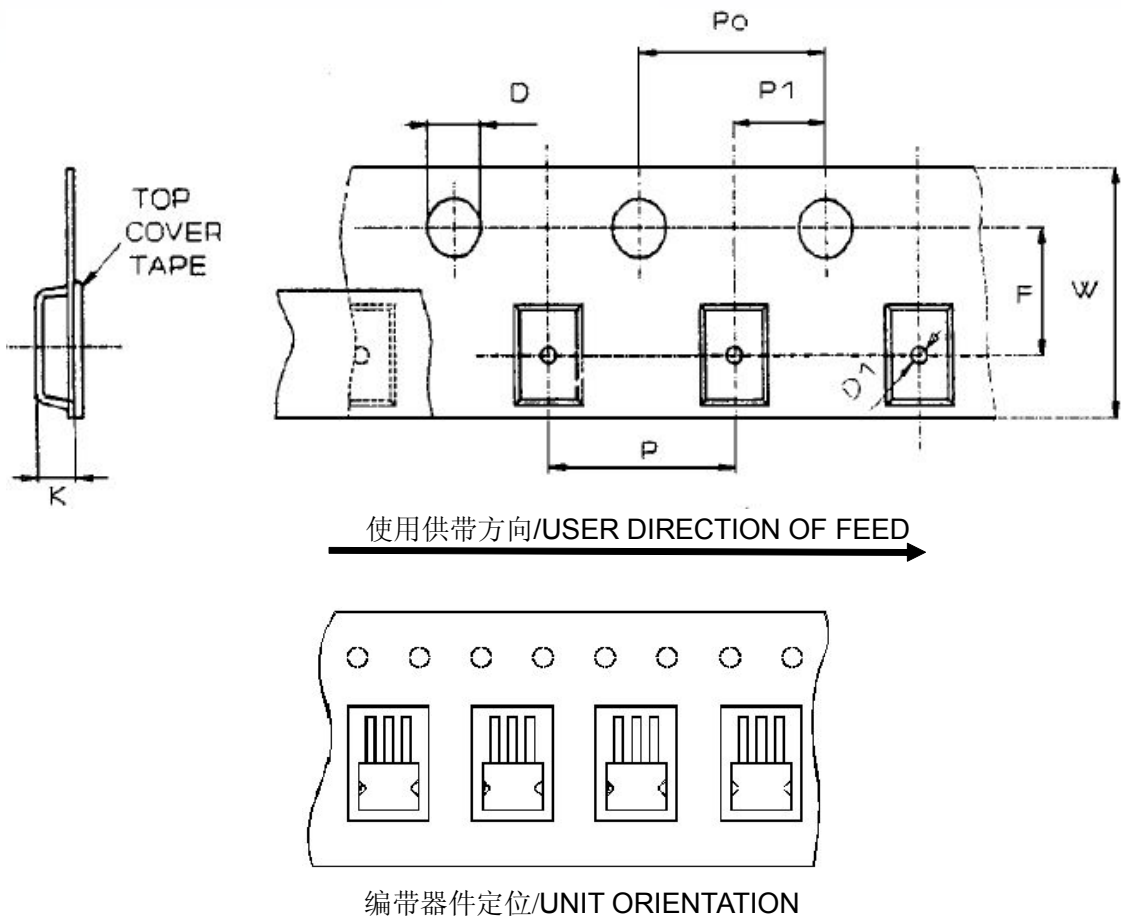


N-沟道功率 MOS 管

TO-252 编带规格尺寸
TO-252 TAPE AND REEL DATA

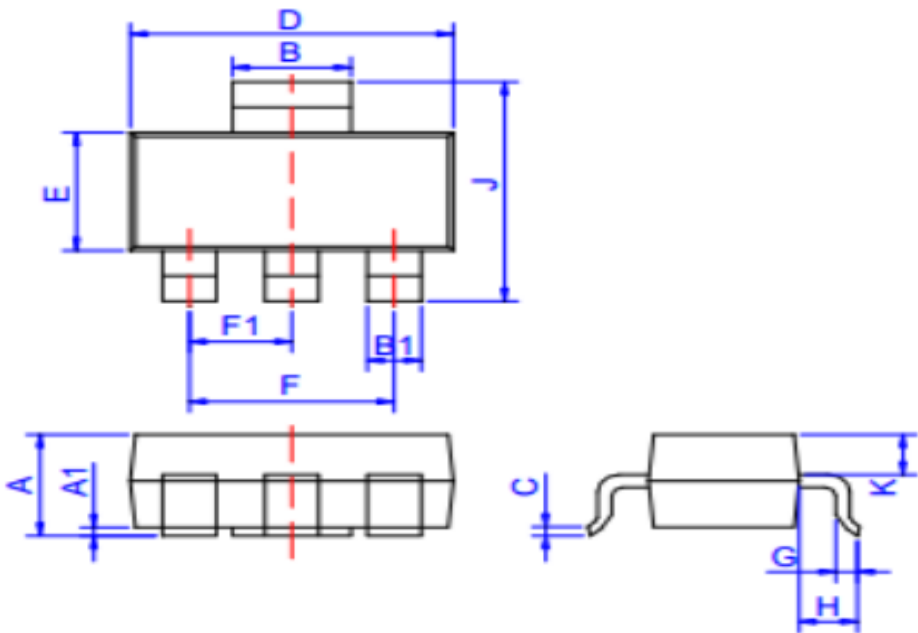
单位:毫米/UNIT: mm

符号 SYMBOL	最小值 min	最大值 max	符号 SYMBOL	最小值 min	最大值 max
W	16.0-0.3	16.0+0.3	F	7.5-0.1	7.5+0.1
P0	4.0-0.1	4.0+0.1	D	1.5-0.0	1.5+0.1
P	8.0-0.1	8.0+0.1	P1	2.0-0.1	2.0+0.1
K	2.65	2.80	D1	1.5-0.0	1.5+0.1



SOT-223 封装机械尺寸
SOT-223 MECHANICAL DATA

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	1.5	1.6	1.8	0.059	0.063	0.071
A1	0.01	0.06	0.10	0.001	0.002	0.004
B	2.9	3.0	3.1	0.114	0.118	0.122
B1	0.6	0.7	0.8	0.024	0.028	0.031
C	0.22	0.26	0.32	0.009	0.010	0.013
D	6.3	6.5	6.7	0.248	0.256	0.264
E	3.3	3.5	3.7	0.130	0.138	0.146
F		4.6			0.181	
F1		2.3			0.091	
G	0.7	0.9	1.1	0.028	0.035	0.043
H	1.5	1.75	2	0.059	0.069	0.079
J	6.7	7.0	7.3	0.264	0.276	0.287
K		0.9			0.035	



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